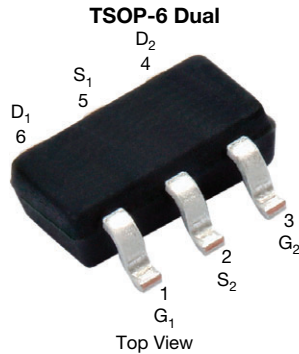


## N- and P-Channel 30 V (D-S) MOSFET

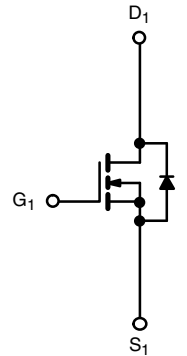


### FEATURES

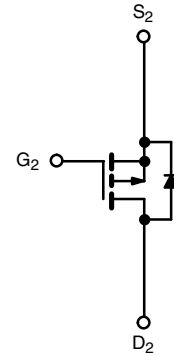
- TrenchFET® power MOSFET
- 100 % R<sub>g</sub> tested
- Material categorization:  
for definitions of compliance please see  
[www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available



N-Channel MOSFET



P-Channel MOSFET

### PRODUCT SUMMARY

|                                                      | N-CHANNEL     | P-CHANNEL |
|------------------------------------------------------|---------------|-----------|
| V <sub>DS</sub> (V)                                  | 30            | -30       |
| R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = ± 10 V  | 0.105         | 0.200     |
| R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = ± 4.5 V | 0.175         | 0.360     |
| Q <sub>g</sub> typ. (nC)                             | 2.1           | 2.4       |
| I <sub>D</sub> (A) <sup>a</sup>                      | 2.5           | -1.8      |
| Configuration                                        | N- and p-pair |           |

### ORDERING INFORMATION

|                                 |                 |
|---------------------------------|-----------------|
| Package                         | TSOP-6          |
| Lead (Pb)-free                  | Si3552DV-T1-E3  |
| Lead (Pb)-free and halogen-free | Si3552DV-T1-GE3 |

### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)

| PARAMETER                                               |                        | SYMBOL                            | N-CHANNEL   | P-CHANNEL | UNIT |
|---------------------------------------------------------|------------------------|-----------------------------------|-------------|-----------|------|
| Drain-source voltage                                    |                        | V <sub>DS</sub>                   | 30          | -30       | V    |
| Gate-source voltage                                     |                        | V <sub>GS</sub>                   | ± 20        | ± 20      |      |
| Continuous drain current (T <sub>J</sub> = 150 °C) a, b | T <sub>A</sub> = 25 °C | I <sub>D</sub>                    | 2.5         | -1.8      | A    |
|                                                         | T <sub>A</sub> = 70 °C |                                   | 2           | -1.2      |      |
| Pulsed drain current                                    |                        | I <sub>DM</sub>                   | 8           | -7        |      |
| Continuous source current (diode conduction) a, b       |                        | I <sub>S</sub>                    | 1.05        | -1.05     |      |
| maximum power dissipation a, b                          | T <sub>A</sub> = 25 °C | P <sub>D</sub>                    | 1.15        |           | W    |
|                                                         | T <sub>A</sub> = 70 °C |                                   | 0.73        |           |      |
| Operating junction and storage temperature range        |                        | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150 |           | °C   |

### THERMAL RESISTANCE RATINGS

| PARAMETER                                | SYMBOL            | TYPICAL | MAXIMUM | UNIT |
|------------------------------------------|-------------------|---------|---------|------|
| Maximum junction-to-ambient <sup>a</sup> | R <sub>thJA</sub> | 93      | 110     | °C/W |
|                                          |                   | 130     | 150     |      |
| Maximum junction-to-lead                 | R <sub>thJL</sub> | 75      | 90      |      |

#### Notes

- a. Surface mounted on FR4 board  
b. t ≤ 5 s



| SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted) |                     |                                                                                                                                                                                                                                                                               |      |      |       |       |      |
|-----------------------------------------------------------------|---------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------|------|-------|-------|------|
| PARAMETER                                                       | SYMBOL              | TEST CONDITIONS                                                                                                                                                                                                                                                               |      | MIN. | TYP.  | MAX.  | UNIT |
| Static                                                          |                     |                                                                                                                                                                                                                                                                               |      |      |       |       |      |
| Gate threshold voltage                                          | V <sub>GS(th)</sub> | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                                                                                                                                                                                                   | N-Ch | 1    | -     | -     | V    |
|                                                                 |                     | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA                                                                                                                                                                                                                  | P-Ch | -1   | -     | -     |      |
| Gate-body leakage                                               | I <sub>GSS</sub>    | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V                                                                                                                                                                                                                               | N-Ch | -    | -     | ± 100 | nA   |
|                                                                 |                     |                                                                                                                                                                                                                                                                               | P-Ch | -    | -     | ± 100 |      |
| Zero gate voltage drain current                                 | I <sub>DSS</sub>    | V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V                                                                                                                                                                                                                                 | N-Ch | -    | -     | 1     | μA   |
|                                                                 |                     | V <sub>DS</sub> = -24 V, V <sub>GS</sub> = 0 V                                                                                                                                                                                                                                | P-Ch | -    | -     | -1    |      |
|                                                                 |                     | V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C                                                                                                                                                                                                         | N-Ch | -    | -     | 5     |      |
|                                                                 |                     | V <sub>DS</sub> = -24 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C                                                                                                                                                                                                        | P-Ch | -    | -     | -5    |      |
| On-state drain current <sup>a</sup>                             | I <sub>D(on)</sub>  | V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V                                                                                                                                                                                                                                 | N-Ch | 5    | -     | -     | A    |
|                                                                 |                     | V <sub>DS</sub> = -5 V, V <sub>GS</sub> = -10 V                                                                                                                                                                                                                               | P-Ch | -5   | -     | -     |      |
| Drain-source on-state resistance <sup>a</sup>                   | R <sub>DS(on)</sub> | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.5 A                                                                                                                                                                                                                                | N-Ch | -    | 0.085 | 0.105 | Ω    |
|                                                                 |                     | V <sub>GS</sub> = -10 V, I <sub>D</sub> = -1.8 A                                                                                                                                                                                                                              | P-Ch | -    | 0.165 | 0.200 |      |
|                                                                 |                     | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 2 A                                                                                                                                                                                                                                 | N-Ch | -    | 0.140 | 0.175 |      |
|                                                                 |                     | V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -1.2 A                                                                                                                                                                                                                             | P-Ch | -    | 0.298 | 0.360 |      |
| Forward transconductance <sup>a</sup>                           | g <sub>fs</sub>     | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 2.5 A                                                                                                                                                                                                                                | N-Ch | -    | 4.3   | -     | S    |
|                                                                 |                     | V <sub>DS</sub> = -15 V, I <sub>D</sub> = -1.8 A                                                                                                                                                                                                                              | P-Ch | -    | 2.4   | -     |      |
| Diode forward voltage <sup>a</sup>                              | V <sub>SD</sub>     | I <sub>S</sub> = 1.05 A, V <sub>GS</sub> = 0 V                                                                                                                                                                                                                                | N-Ch | -    | 0.81  | 1.1   | V    |
|                                                                 |                     | I <sub>S</sub> = -1.05 A, V <sub>GS</sub> = 0 V                                                                                                                                                                                                                               | P-Ch | -    | -0.83 | -1.1  |      |
| Dynamic <sup>b</sup>                                            |                     |                                                                                                                                                                                                                                                                               |      |      |       |       |      |
| Total gate charge                                               | Q <sub>g</sub>      | N-Channel<br>V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 5 V, I <sub>D</sub> = 1.8 A<br><br>P-Channel<br>V <sub>DS</sub> = -15 V, V <sub>GS</sub> = -5 V, I <sub>D</sub> = -1.8 A                                                                                               | N-Ch | -    | 2.1   | 3.2   | nC   |
| Gate-source charge                                              | Q <sub>gs</sub>     |                                                                                                                                                                                                                                                                               | P-Ch | -    | 2.4   | 3.6   |      |
|                                                                 |                     |                                                                                                                                                                                                                                                                               | N-Ch | -    | 0.7   | -     |      |
| Gate-drain charge                                               | Q <sub>gd</sub>     |                                                                                                                                                                                                                                                                               | P-Ch | -    | 0.9   | -     |      |
|                                                                 |                     |                                                                                                                                                                                                                                                                               | N-Ch | -    | 0.7   | -     |      |
|                                                                 |                     |                                                                                                                                                                                                                                                                               | P-Ch | -    | 0.8   | -     |      |
| Gate resistance                                                 | R <sub>g</sub>      | N-Ch                                                                                                                                                                                                                                                                          | 0.5  | -    | 2.4   | Ω     |      |
|                                                                 |                     | P-Ch                                                                                                                                                                                                                                                                          | 3    | -    | 11    |       |      |
| Turn-on delay time                                              | t <sub>d(on)</sub>  | N-Channel<br>V <sub>DD</sub> = 15 V, R <sub>L</sub> = 15 Ω<br>I <sub>D</sub> ≅ 1 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 6 Ω<br><br>P-Channel<br>V <sub>DD</sub> = -15 V, R <sub>L</sub> = 15 Ω<br>I <sub>D</sub> ≅ -1 A, V <sub>GEN</sub> = -10 V, R <sub>g</sub> = 6 Ω | N-Ch | -    | 7     | 11    | ns   |
| Rise time                                                       | t <sub>r</sub>      |                                                                                                                                                                                                                                                                               | P-Ch | -    | 8     | 12    |      |
|                                                                 |                     |                                                                                                                                                                                                                                                                               | N-Ch | -    | 9     | 14    |      |
| Turn-off delay time                                             | t <sub>d(off)</sub> |                                                                                                                                                                                                                                                                               | P-Ch | -    | 12    | 18    |      |
|                                                                 |                     |                                                                                                                                                                                                                                                                               | N-Ch | -    | 13    | 20    |      |
| Fall time                                                       | t <sub>f</sub>      |                                                                                                                                                                                                                                                                               | P-Ch | -    | 12    | 18    |      |
|                                                                 |                     |                                                                                                                                                                                                                                                                               | N-Ch | -    | 5     | 8     |      |
|                                                                 |                     |                                                                                                                                                                                                                                                                               | P-Ch | -    | 7     | 11    |      |
| Source-drain reverse recovery time                              | t <sub>rr</sub>     | I <sub>F</sub> = 1.05 A, di/dt = 100 A/μs                                                                                                                                                                                                                                     | N-Ch | -    | 35    | 60    |      |
|                                                                 |                     | I <sub>F</sub> = -1.05 A, di/dt = 100 A/μs                                                                                                                                                                                                                                    | P-Ch | -    | 30    | 60    |      |

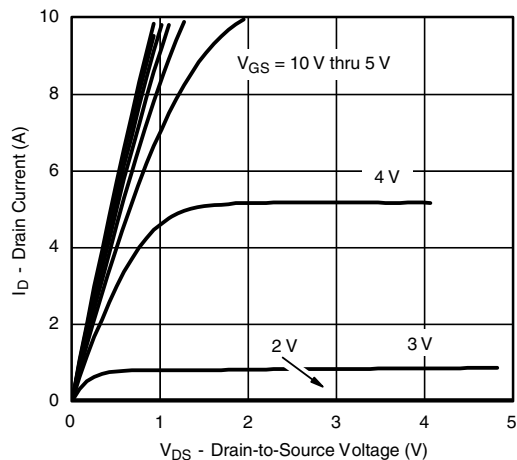
**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing

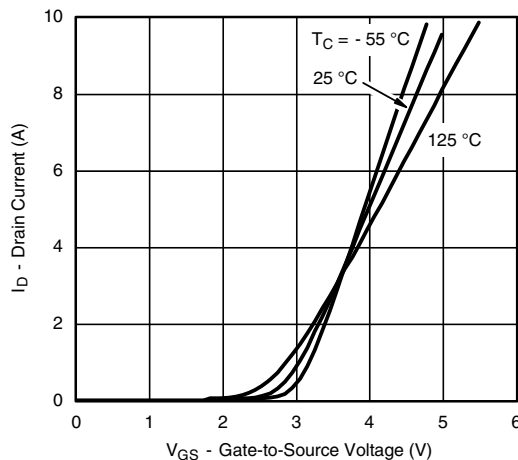
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



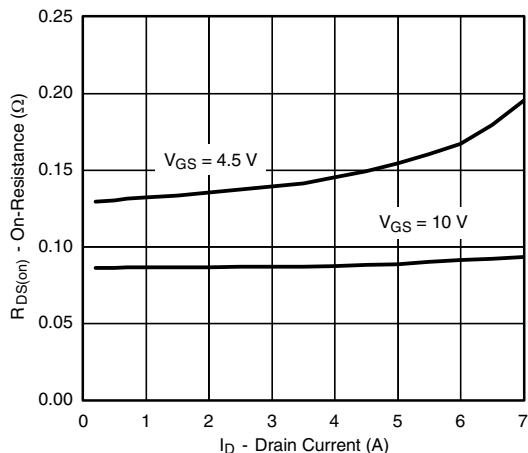
**N-CHANNEL TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



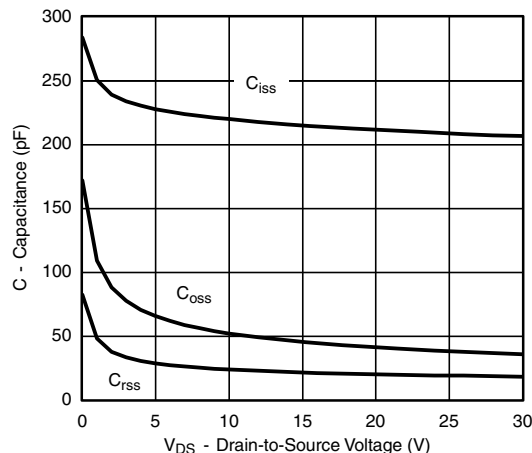
**Output Characteristics**



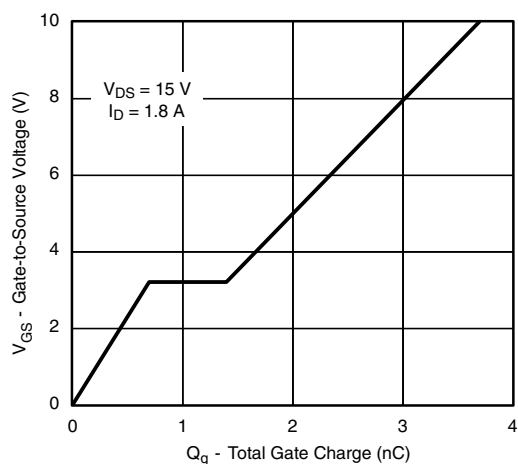
**Transfer Characteristics**



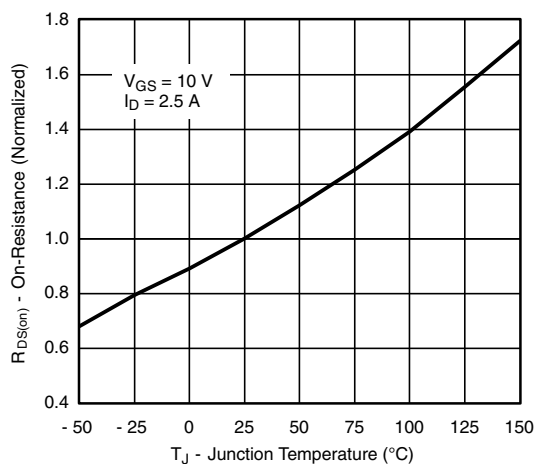
**On-Resistance vs. Drain Current**



**Capacitance**



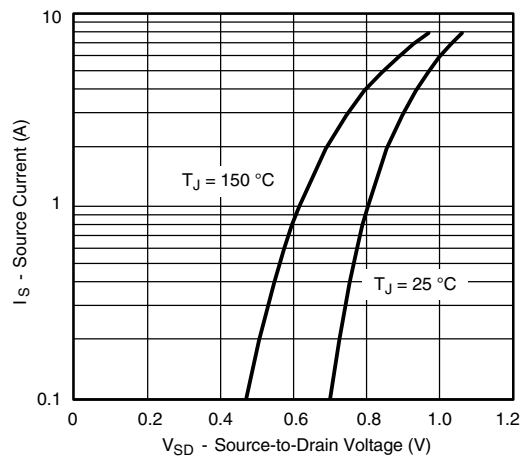
**Gate Charge**



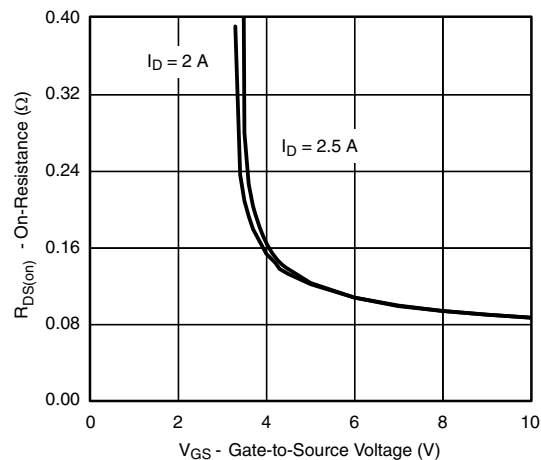
**On-Resistance vs. Junction Temperature**



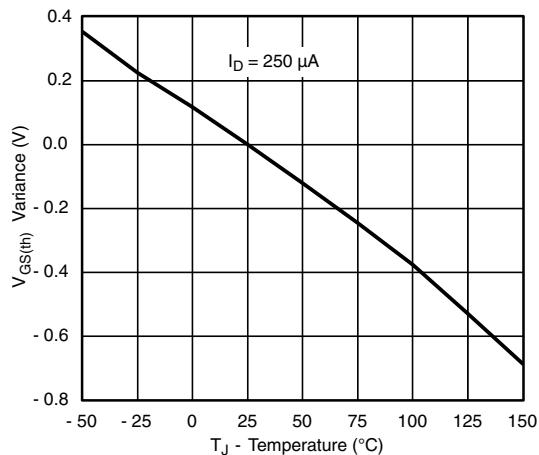
**N-CHANNEL TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



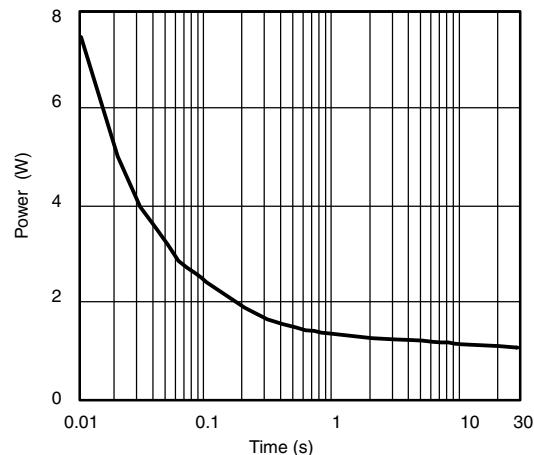
**Source-Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



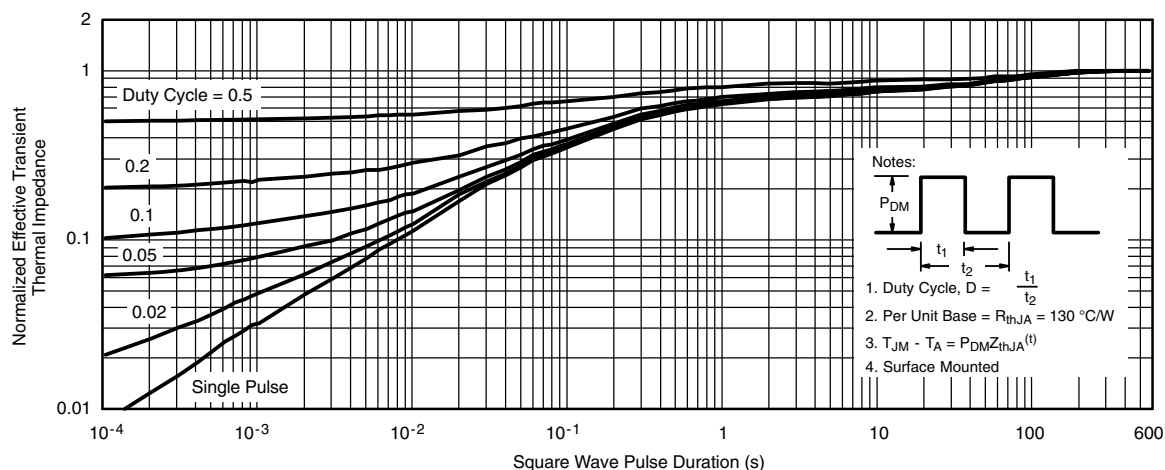
**Threshold Voltage**



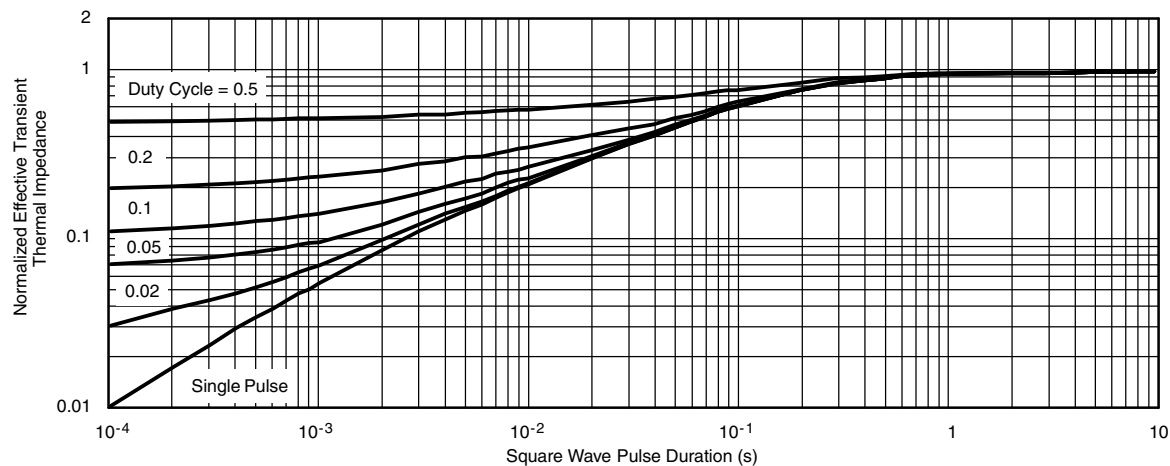
**Single Pulse Power (Junction-to-Ambient)**



**N-CHANNEL TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



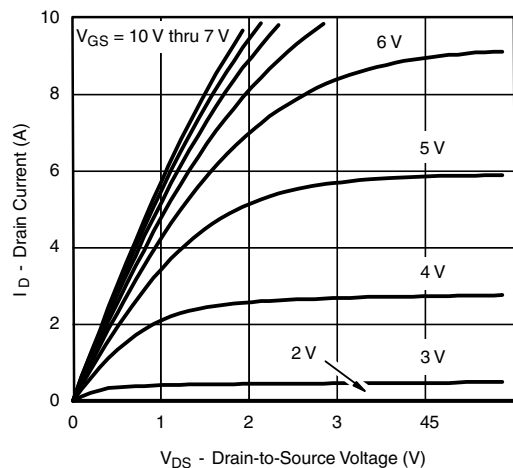
**Normalized Thermal Transient Impedance, Junction-to-Ambient**



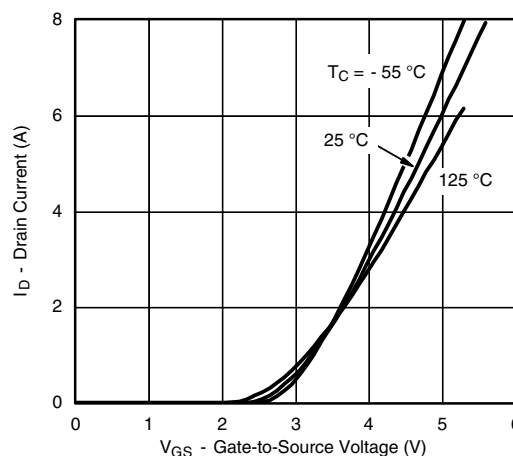
**Normalized Thermal Transient Impedance, Junction-to-Foot**



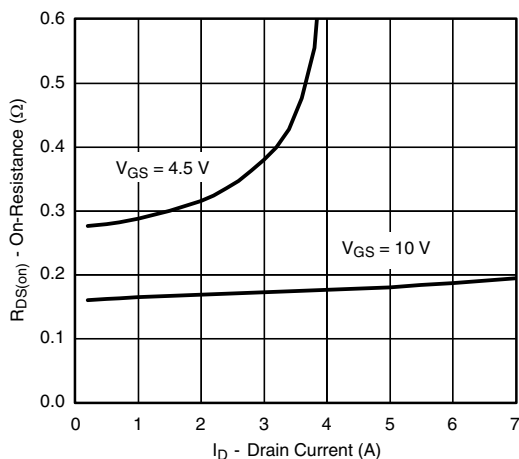
**P-CHANNEL TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



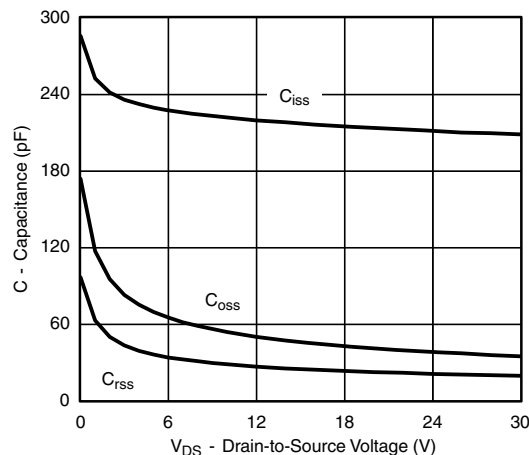
**Output Characteristics**



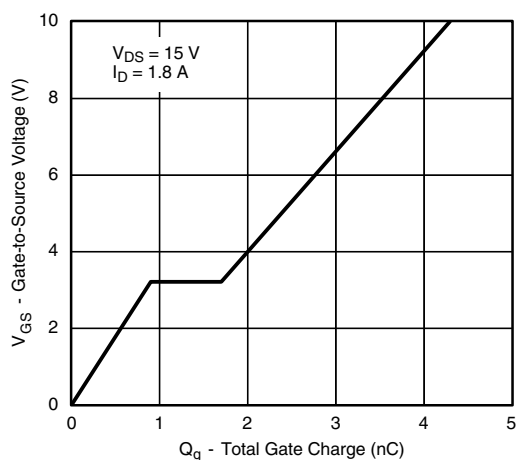
**Transfer Characteristics**



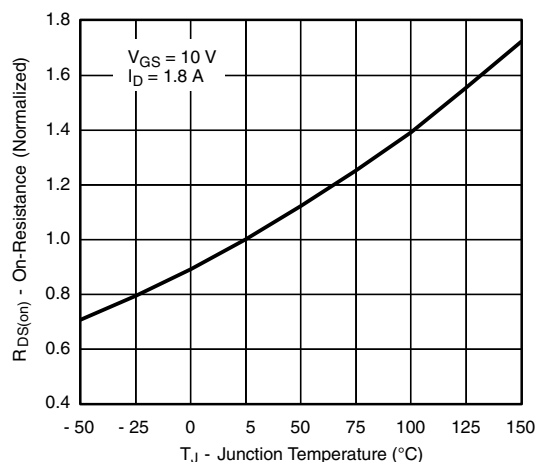
**On-Resistance vs. Drain Current**



**Capacitance**



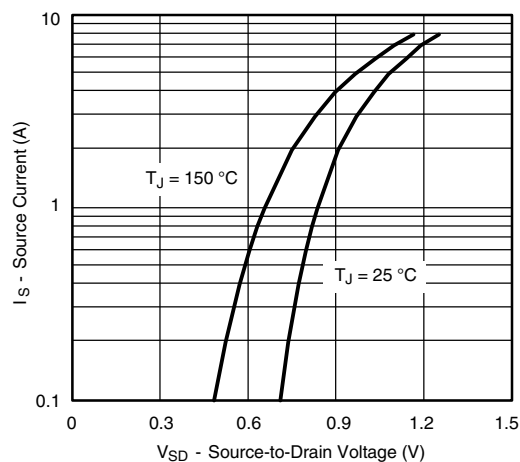
**Gate Charge**



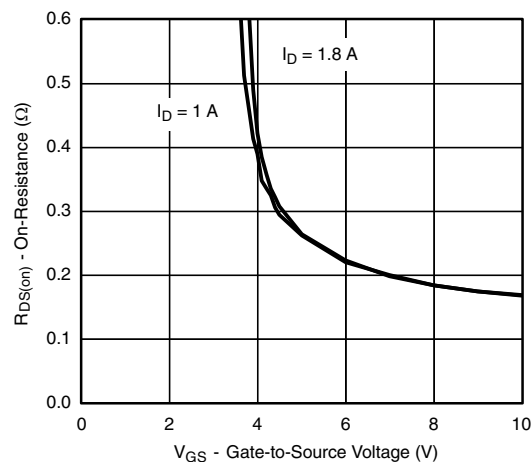
**On-Resistance vs. Junction Temperature**



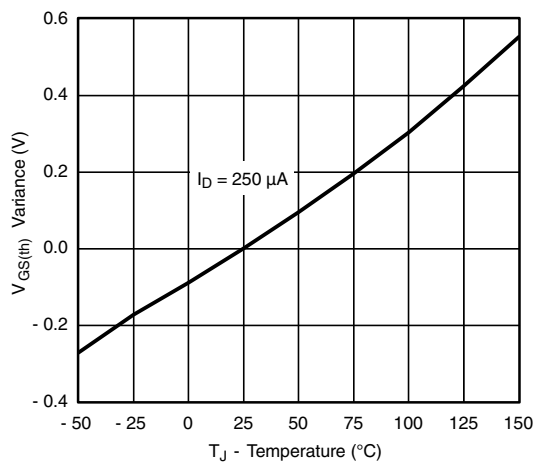
**P-CHANNEL TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



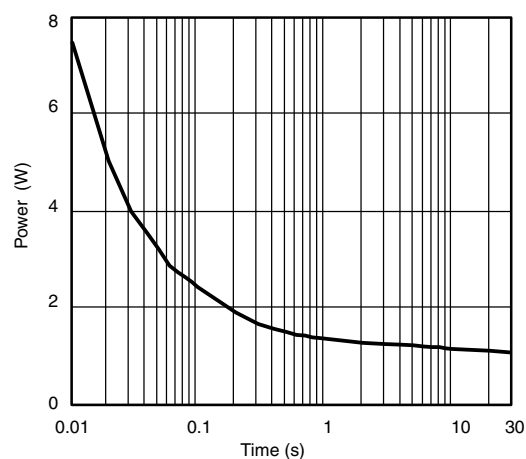
**Source-Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



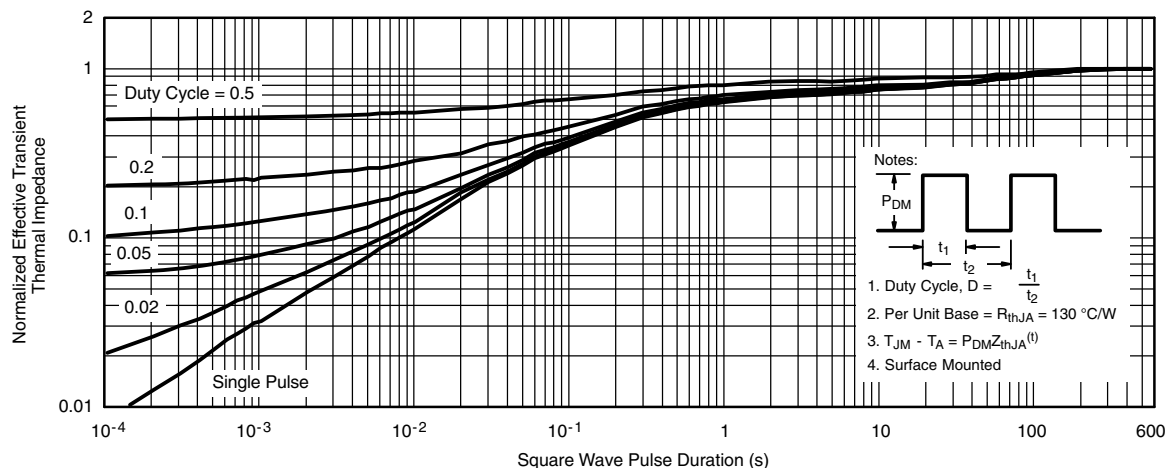
**Threshold Voltage**



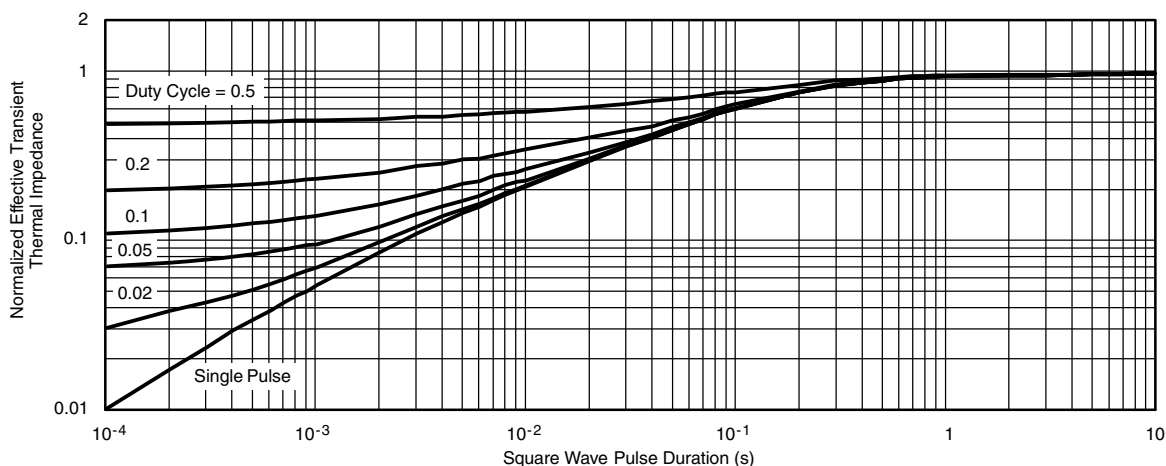
**Single Pulse Power (Junction-to-Ambient)**



**P-CHANNEL TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

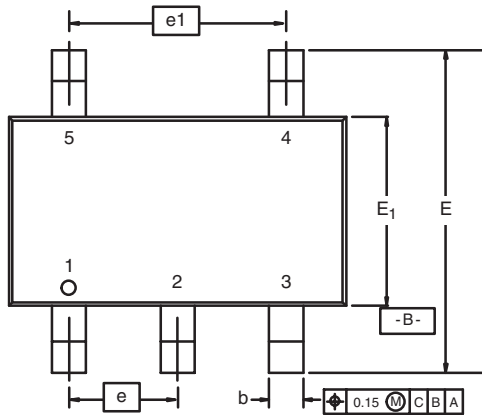


**Normalized Thermal Transient Impedance, Junction-to-Foot**

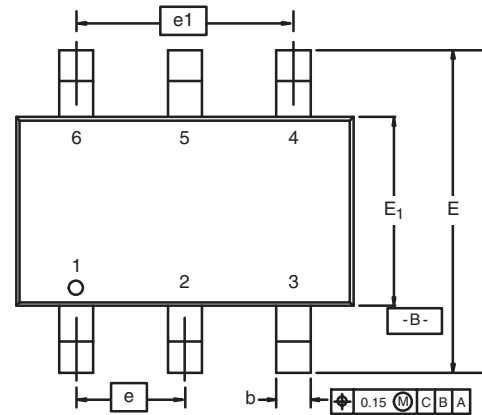
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?70971](http://www.vishay.com/ppg?70971).

## TSOP: 5/6-LEAD

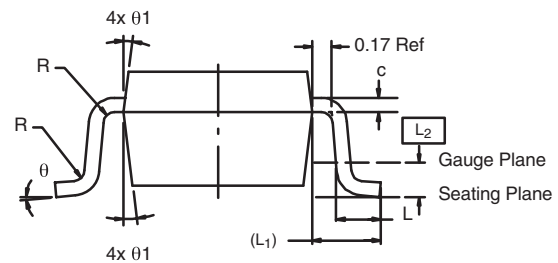
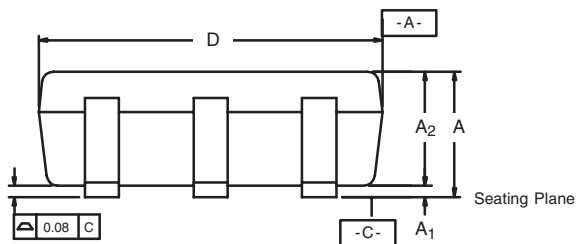
JEDEC Part Number: MO-193C



5-LEAD TSOP

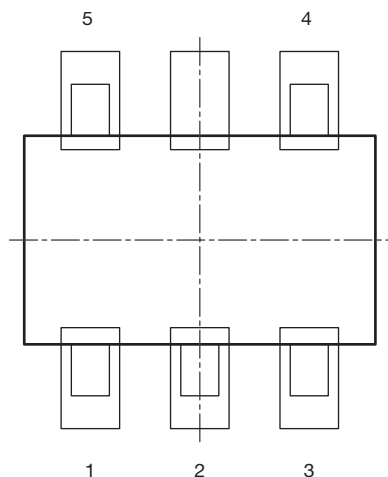


6-LEAD TSOP

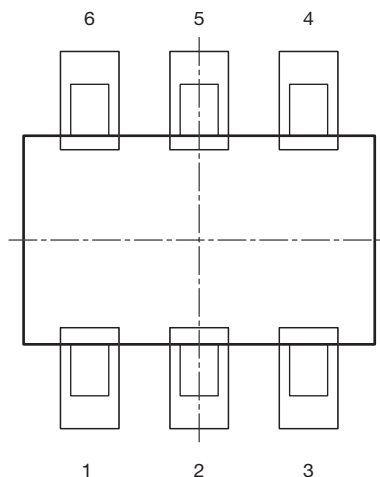


| Dim                            | MILLIMETERS |      |      | INCHES     |       |       |
|--------------------------------|-------------|------|------|------------|-------|-------|
|                                | Min         | Nom  | Max  | Min        | Nom   | Max   |
| A                              | 0.91        | -    | 1.10 | 0.036      | -     | 0.043 |
| A <sub>1</sub>                 | 0.01        | -    | 0.10 | 0.0004     | -     | 0.004 |
| A <sub>2</sub>                 | 0.90        | -    | 1.00 | 0.035      | 0.038 | 0.039 |
| b                              | 0.30        | 0.32 | 0.45 | 0.012      | 0.013 | 0.018 |
| c                              | 0.10        | 0.15 | 0.20 | 0.004      | 0.006 | 0.008 |
| D                              | 2.95        | 3.05 | 3.10 | 0.116      | 0.120 | 0.122 |
| E                              | 2.70        | 2.85 | 2.98 | 0.106      | 0.112 | 0.117 |
| E <sub>1</sub>                 | 1.55        | 1.65 | 1.70 | 0.061      | 0.065 | 0.067 |
| e                              | 0.95 BSC    |      |      | 0.0374 BSC |       |       |
| e <sub>1</sub>                 | 1.80        | 1.90 | 2.00 | 0.071      | 0.075 | 0.079 |
| L                              | 0.32        | -    | 0.50 | 0.012      | -     | 0.020 |
| L <sub>1</sub>                 | 0.60 Ref    |      |      | 0.024 Ref  |       |       |
| L <sub>2</sub>                 | 0.25 BSC    |      |      | 0.010 BSC  |       |       |
| R                              | 0.10        | -    | -    | 0.004      | -     | -     |
| θ                              | 0°          | 4°   | 8°   | 0°         | 4°    | 8°    |
| θ <sub>1</sub>                 | 7° Nom      |      |      | 7° Nom     |       |       |
| ECN: C-06593-Rev. I, 18-Dec-06 |             |      |      |            |       |       |
| DWG: 5540                      |             |      |      |            |       |       |

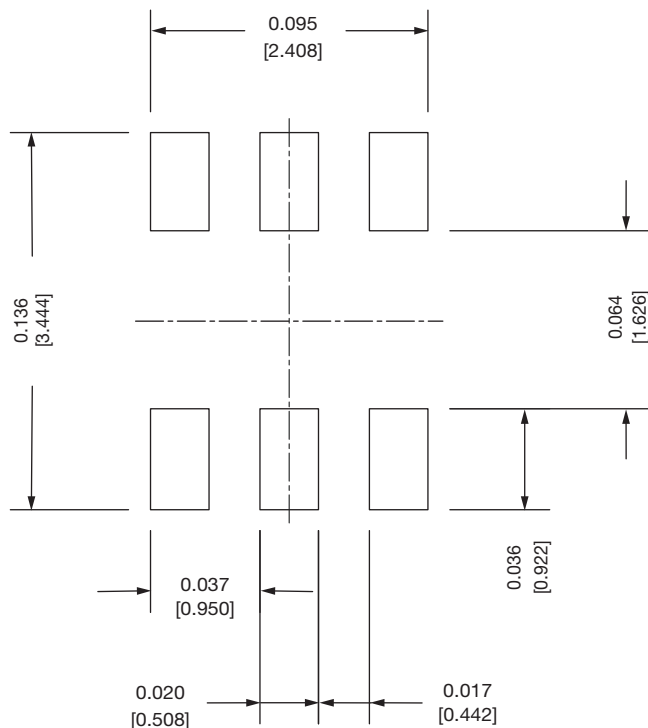
## Recommended Land Pattern For TSOP-5L / TSOP-6L



TSOP 5L



TSOP 6L


**Note**

- All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022  
DWG: 3010



## Disclaimer

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